

**Ultra Linear Driver Amplifier - 1 Watt
1800 to 2000 MHz**

PA2001

V1

Features

- LOW NOISE FIGURE: 2.0 dB (TYP.)
- GAIN: 21 dB (TYP.)
- HIGH P1dB: +30.3 dBm (TYP.)
- HIGH IP³: +46.5 dBm (TYP.)
- BROADBAND RESPONSE: 1.5 GHz TO 2.2 GHz (TYP.)

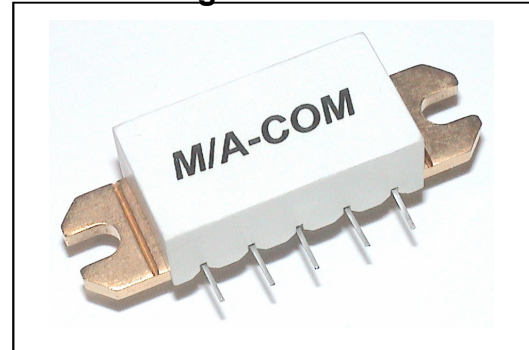
Description

The PA2001 is a discrete hybrid design, which uses thick film solder manufacturing processes for accurate performance and high reliability.

This 2 stage GaAs FET transistor design uses feedback loops for flat broadband linear performance, with very low noise figure.

The model is particularly suited for power driver applications used in the base station & repeater infrastructure, and for commercial & military radios.

Product Image



Ordering Information

Part Number	Package
PA2001	Flange Mount Carrier

Absolute Maximum Ratings

Parameter	Absolute Maximum
Storage Temperature	-40°C to +85°C
Operation Base Temperature	+85°C
Max. DC Voltage	+15 Vdc
Max. Continuous RF Input Power	+15 dBm

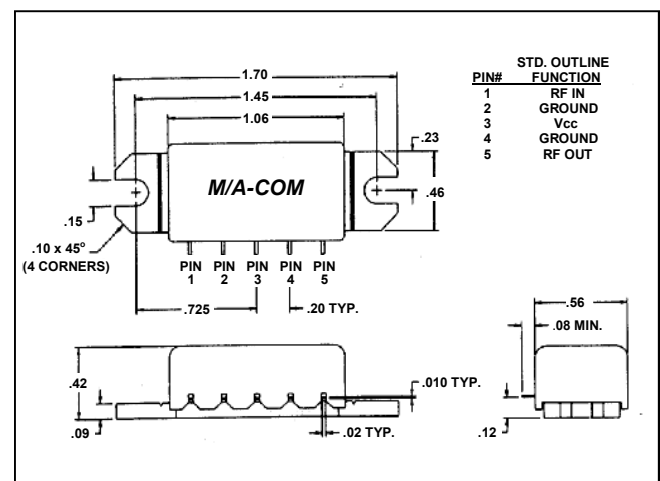
Electrical Specifications: Z₀ = 50Ω, V_{CC} = +12 V_{DC}

Parameter	Units	Typical	Guaranteed
		25°C	0°C to +85°C
Frequency	MHz	1800-2000	1800-2000
Small Signal Gain (min)	dB	21.0	19.0
Gain Flatness (max)	dB	± 0.2	± 0.4
Noise Figure (max)	dB	2.0	3.5
Reverse Isolation	dB	37.0	
Power Output @ 1.0 dB Comp. (min.)	dBm	+30.3	+29.0
Output IP ³	dBm	+46.5	+43.0
VSWR Input / Output (max.)		1.2:1 / 1.6:1	2.0:1 / 2.0:1
DC Current @ +12 Volts (max.)	mA	345	400

Thermal Data: V_{CC} = +12 V_{DC}

Parameter	Rating
Thermal Resistance θ _{jc}	22°C/W
Junction Temperature Rise Above Case T _{jc}	51°C

Outline Drawing: Flange Mount Carrier *



* Dimensions are inches ± 0.015 unless otherwise specified.